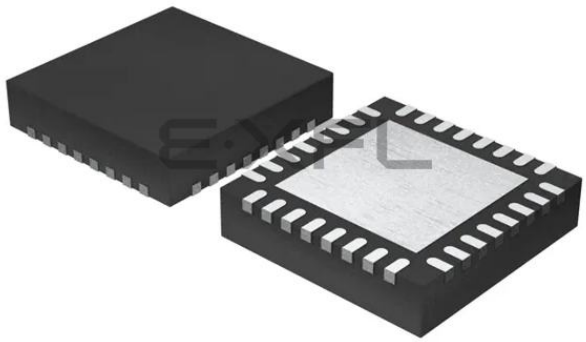

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, SPI, UART/USART, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 6x12b; D/A 1x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount, Wettable Flank
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf51ju32vfm

Table of Contents

Field	Description	Values
MMM	Memory size (program flash memory)[1]	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB
T	Temperature range, ambient (°C)	V = –40 to 105
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • HS = 44 Laminate QFN (5 mm x 5 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm)

1. All parts also have FlexNVM, FlexRAM, and RAM.

2.4 Example

This is an example part number:

MCF51JU128VLH

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{DIO}	Digital input voltage (except $\overline{\text{RESET}}$, EXTAL, and XTAL)	–0.3	V_{DD} + 0.3	V
V_{AIO}	Analog, $\overline{\text{RESET}}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{USB_DP}	USB_DP input voltage	–0.3	3.63	V
V_{USB_DM}	USB_DM input voltage	–0.3	3.63	V
VREGIN	USB Regulator input	–0.3	6.0	V

5 General

5.1 Typical Value Conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C

Table continues on the next page...

5.2.2 LVD and POR operating requirements

Table 2. LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period factory trimmed	900	1000	1100	µs	

1. Rising thresholds are falling threshold + hysteresis voltage

5. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash memory.
6. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks enabled, but peripherals are not in active operation. Code executing from flash memory.
7. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks disabled.
8. OSC clocks disabled.
9. All pads disabled.
10. Data reflects devices with 32 KB of RAM. For devices with 16 KB of RAM, power consumption is reduced by 500 nA. For devices with 8 KB of RAM, power consumption is reduced by 750 nA.
11. RTC function current includes LPTMR with OSC enabled with 32.768 kHz crystal at 3.0 V

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode, except for 50 MHz core (FEI mode)
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL
- For the ALLON curve, all peripheral clocks are enabled, but peripherals are not in active operation
- USB Voltage Regulator disabled
- No GPIOs toggled
- Code execution from flash memory with cache enabled

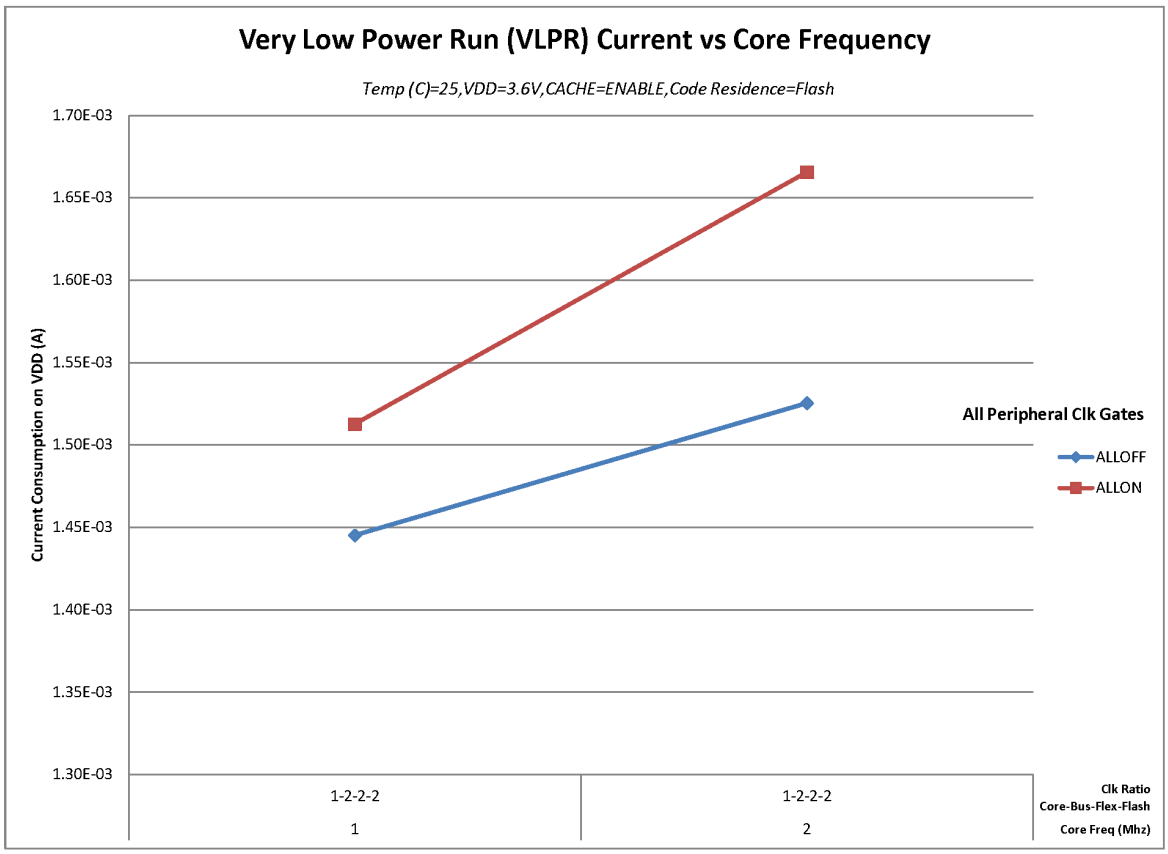

Figure 2. VLPR mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 6. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	20	dBµV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	19		
V_{RE3}	Radiated emissions voltage, band 3	150–500	17		
V_{RE4}	Radiated emissions voltage, band 4	500–1000	16		
V_{RE_IEC}	IEC level	0.15–1000	L	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions*, and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*.

5.3.1 General Switching Specifications

These general purpose specifications apply to all signals configured for EGPIO, MTIM, CMT, PDB, IRQ, and I^2C signals. The conditions are 50 pf load, V_{DD} = 1.71 V to 3.6 V, and full temperature range. The GPIO are set for high drive, no slew rate control, and no input filter, digital or analog, unless otherwise specified.

Table 9. EGPIO General Control Timing

Symbol	Description	Min.	Max.	Unit
G1	Bus clock from CLK_OUT pin high to GPIO output valid	—	32	ns
G2	Bus clock from CLK_OUT pin high to GPIO output invalid (output hold)	1	—	ns
G3	GPIO input valid to bus clock high	28	—	ns
G4	Bus clock from CLK_OUT pin high to GPIO input invalid	—	4	ns
	GPIO pin interrupt pulse width (digital glitch filter disabled) Synchronous path[1]	1.5	—	Bus clock cycles
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) Asynchronous path[2]	100	—	ns
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) Asynchronous path[2]	50	—	ns
	External reset pulse width (digital glitch filter disabled)	100	—	ns
	Mode select (MS) hold time after reset deassertion	2	—	Bus clock cycles

1. The greater synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.

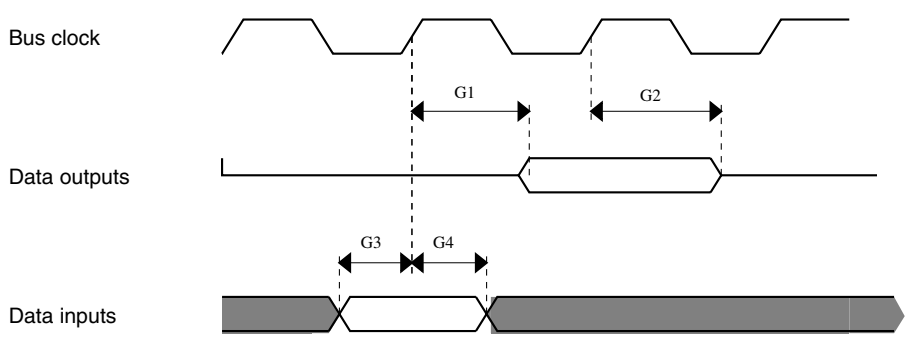

Figure 3. EGPIO timing diagram

The following general purpose specifications apply to all signals configured for RGPIO, FTM, and UART. The conditions are 25 pf load, V_{DD} = 3.6 V to 1.71 V, and full temperature range. The GPIO are set for high drive, no slew rate control, and no input filter, digital or analog, unless otherwise specified.

Table 10. RGPIO General Control Timing

Symbol	Description	Min.	Max.	Unit
R1	CPUCLK from CLK_OUT pin high to GPIO output valid	—	16	ns
R2	CPUCLK from CLK_OUT pin high to GPIO output invalid (output hold)	1	—	ns
R3	GPIO input valid to bus clock high	17	—	ns
R4	CPUCLK from CLK_OUT pin high to GPIO input invalid	—	2	ns

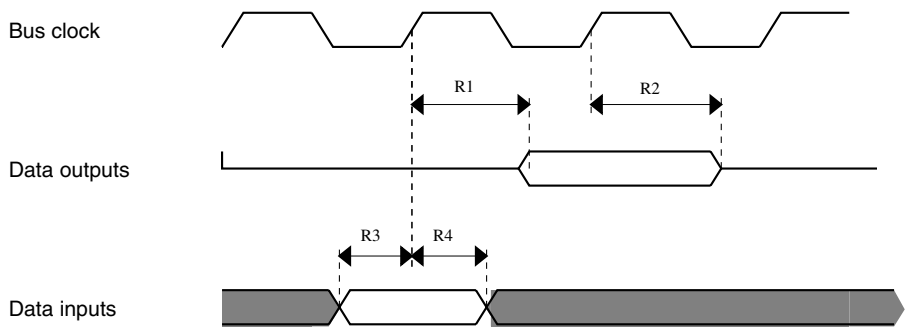

Figure 4. RGPIO timing diagram

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	115	°C
T_A	Ambient temperature	–40	105	°C

5.4.2 Thermal attributes

Board type	Symbol	Description	64 LQFP	48 LQFP	44 Laminate QFN	32 QFN	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	73	79	108	98	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	54	55	69	33	°C/W	1
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	61	66	91	81	°C/W	1
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	48	48	63	28	°C/W	1
—	$R_{\theta JB}$	Thermal resistance, junction to board	37	34	44	13	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	20	20	31	2.2	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	5.0	4.0	6.0	6.0	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions —Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions —Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions —Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 Debug specifications

Table 12. Background debug mode (BDM) timing

Number	Symbol	Description	Min.	Max.	Unit
1	t_{MSSU}	BKGD/MS setup time after issuing background debug force reset to enter user mode or BDM	500	—	ns
2	t_{MSH}	BKGD/MS hold time after issuing background debug force reset to enter user mode or BDM[1]	100	—	µs

Table 13. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
D_{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D_{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t_{pll_lock}	Lock detector detection time	—	—	$150 \times 10^{-6} + 1075(1/f_{pll\_ref})$	s	9

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
3. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
4. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
5. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
6. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
7. Excludes any oscillator currents that are also consuming power while PLL is in operation.
8. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
9. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.3.2 Oscillator electrical specifications

This section provides the electrical characteristics of the module.

6.3.2.1 Oscillator DC electrical specifications

Table 14. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 1 MHz	—	200	—	µA	
	• 4 MHz	—	200	—	µA	
	• 8 MHz (RANGE=01)	—	300	—	µA	
	• 16 MHz	—	950	—	µA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	

Table continues on the next page...

Table 14. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using either the integrated capacitors or by using external components.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.2.2 Oscillator frequency specifications

Table 15. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	1	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.

Table 17. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Longword-write to FlexRAM execution time:					
$t_{eewr32b8k}$	• 8 KB EEPROM backup	—	545	1950	µs	
$t_{eewr32b16k}$	• 16 KB EEPROM backup	—	630	2050	µs	
$t_{eewr32b32k}$	• 32 KB EEPROM backup	—	810	2250	µs	

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.4.1.3 Flash (FTFL) current and power specfications

Table 18. Flash (FTFL) current and power specfications

Symbol	Description	Typ.	Unit
I_{DD_PGM}	Worst case programming current in program flash	10	mA

6.4.1.4 Reliability specifications

Table 19. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	2
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	10	100	—	years	2
$t_{nvmretp100}$	Data retention after up to 100 cycles	15	100	—	years	2
$n_{nvmcycp}$	Cycling endurance	10 K	35 K	—	cycles	3
Data Flash						
$t_{nvmretd10k}$	Data retention after up to 10 K cycles	5	50	—	years	2
$t_{nvmretd1k}$	Data retention after up to 1 K cycles	10	100	—	years	2
$t_{nvmretd100}$	Data retention after up to 100 cycles	15	100	—	years	2
$n_{nvmcycd}$	Cycling endurance	10 K	35 K	—	cycles	3
FlexRAM as EEPROM						
$t_{nvmretee100}$	Data retention up to 100% of write endurance	5	50	—	years	2
$t_{nvmretee10}$	Data retention up to 10% of write endurance	10	100	—	years	2
$t_{nvmretee1}$	Data retention up to 1% of write endurance	15	100	—	years	2

Table continues on the next page...

Table 19. NVM reliability specifications (continued)

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
	Write endurance					4
$n_{nvmwree16}$	• EEPROM backup to FlexRAM ratio = 16	35 K	175 K	—	writes	
$n_{nvmwree128}$	• EEPROM backup to FlexRAM ratio = 128	315 K	1.6 M	—	writes	
$n_{nvmwree512}$	• EEPROM backup to FlexRAM ratio = 512	1.27 M	6.4 M	—	writes	
$n_{nvmwree4k}$	• EEPROM backup to FlexRAM ratio = 4096	10 M	50 M	—	writes	
$n_{nvmwree8k}$	• EEPROM backup to FlexRAM ratio = 8192	20 M	100 M	—	writes	

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology.
2. Data retention is based on T_{javg} = 55°C (temperature profile over the lifetime of the application).
3. Cycling endurance represents number of program/erase cycles at -40°C ≤ T_j ≤ 125°C.
4. Write endurance represents the number of writes to each FlexRAM location at -40°C ≤Tj ≤ 125°C influenced by the cycling endurance of the FlexNVM (same value as data flash) and the allocated EEPROM backup. Minimum and typical values assume all byte-writes to FlexRAM.

6.4.1.5 Write endurance to FlexRAM for EEPROM

When the FlexNVM partition code is not set to full data flash, the EEPROM data set size can be set to any of several non-zero values.

The bytes not assigned to data flash via the FlexNVM partition code are used by the FTFL to obtain an effective endurance increase for the EEPROM data. The built-in EEPROM record management system raises the number of program/erase cycles that can be attained prior to device wear-out by cycling the EEPROM data through a larger EEPROM NVM storage space.

While different partitions of the FlexNVM are available, the intention is that a single choice for the FlexNVM partition code and EEPROM data set size is used throughout the entire lifetime of a given application. The EEPROM endurance equation and graph shown below assume that only one configuration is ever used.

$$\text{Writes\_FlexRAM} = \frac{\text{EEPROM} - 2 \times \text{EEESIZE}}{\text{EEESIZE}} \times \text{Write\_efficiency} \times n_{nvmcycd}$$

where

- Writes_FlexRAM — minimum number of writes to each FlexRAM location
- EEPROM — allocated FlexNVM based on DEPART; entered with Program Partition command
- EEESIZE — allocated FlexRAM based on DEPART; entered with Program Partition command
- Write_efficiency —

The following timing numbers indicate when data is latched or driven onto the external bus, relative to the Mini-Flexbus output clock (FB_CLK). All other timing relationships can be derived from these values.

Table 21. Flexbus switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	
	Frequency of operation	—	25	MHz	
FB1	Clock period	40	—	ns	
FB2	Address, data, and control output valid	—	20	ns	1
FB3	Address, data, and control output hold	1	—	ns	1
FB4	Data and $\overline{\text{FB\_TA}}$ input setup	20	—	ns	2
FB5	Data and $\overline{\text{FB\_TA}}$ input hold	10	—	ns	2

1. Specification is valid for all FB_AD[31:0], $\overline{\text{FB\_CS}}n$, $\overline{\text{FB\_OE}}$, FB_R/$\overline{\text{W}}$, and $\overline{\text{FB\_TS}}$.
2. Specification is valid for all FB_AD[31:0].

Note

The following diagrams refer to signal names that may not be included on your particular device. Ignore these extraneous signals.

Also, ignore the AA=0 portions of the diagrams because this setting is not supported in the Mini-FlexBus.

6.6 Analog

6.6.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

6.6.1.1 12-bit ADC operating conditions

Table 22. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD}-V_{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} (V_{SS}-V_{SSA})	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	Reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 8/10/12 bit modes	— —	4	5	pF	
R_{ADIN}	Input resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance	12 bit modes f_{ADCK} < 4MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 12 bit modes	1.0	—	18.0	MHz	4
C_{rate}	ADC conversion rate	≤ 12 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. The analog source resistance should be kept as low as possible in order to achieve the best results. The results in this datasheet were derived from a system which has <8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to <1ns.
4. To use the maximum ADC conversion clock frequency, the ADHSC bit should be set and the ADLPC bit should be clear.

5. Calculated by a best fit curve from V_{SS}+100 mV to V_{DACR}–100 mV
6. VDDA = 3.0V, reference select set for VDDA (DACx_CO:DACRFS = 1), high power mode(DACx_C0:LPEN = 0), DAC set to 0x800, Temp range from -40C to 105C

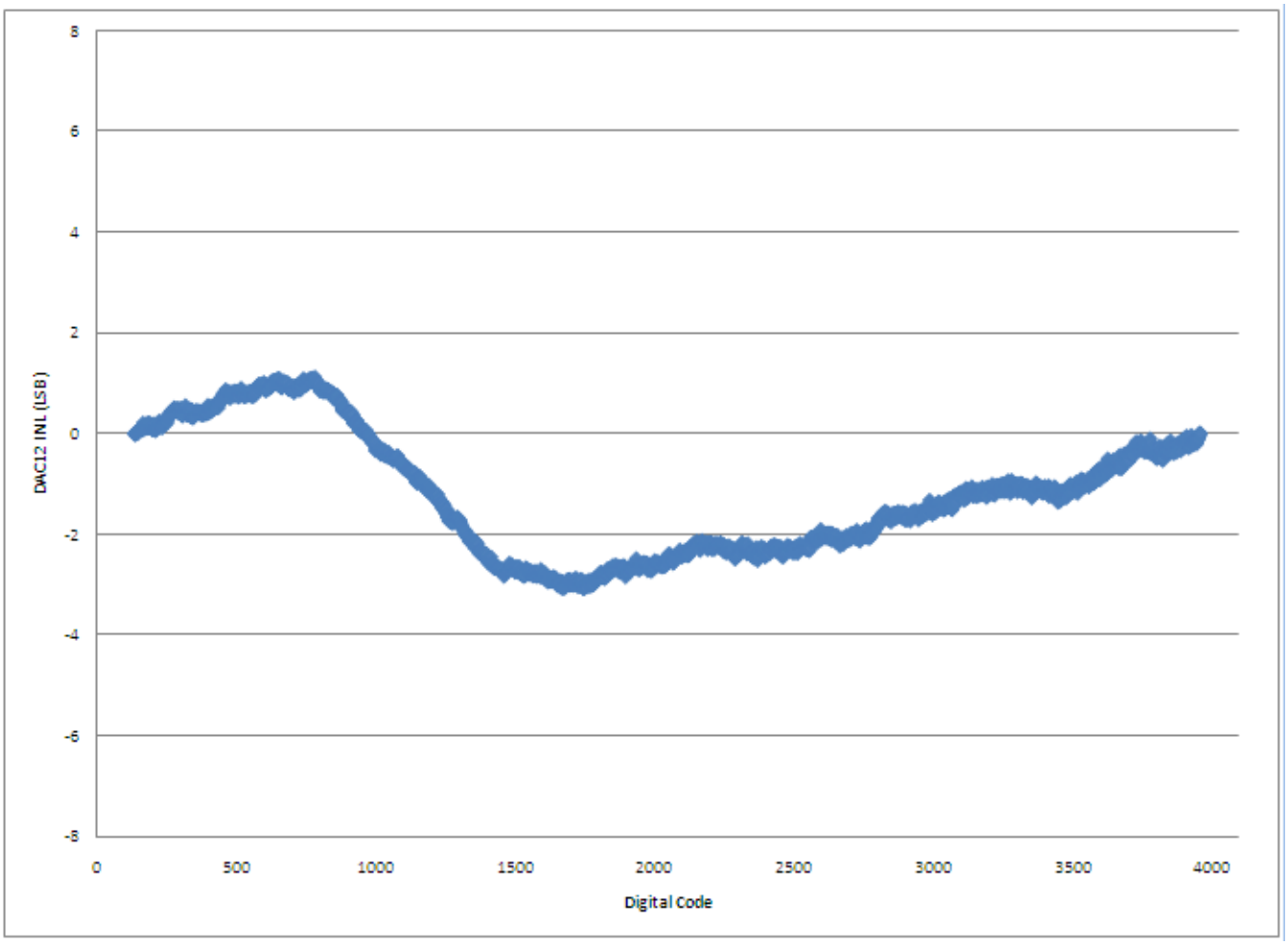

Figure 12. Typical INL error vs. digital code

Table 32. USB VREG electrical specifications (continued)

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) > 3.6 V					
	• Run mode	3	3.3	3.6	V	
	• Standby mode	2.1	2.8	3.6	V	
$V_{Reg33out}$	Regulator output voltage — Input supply (VREGIN) < 3.6 V, pass-through mode	2.1	—	3.6	V	2
C_{OUT}	External output capacitor	1.76	2.2	8.16	µF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I_{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.
2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

6.8.4 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 70% V_{DD}, unless noted, as well as input signal transitions of 3 ns and a 50 pF maximum load on all SPI pins. All timing assumes slew rate control is disabled and high drive strength is enabled for SPI output pins.

Table 33. SPI master mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	f_{BUS}/2048	f_{BUS}/2	Hz	f_{BUS} is the bus clock as defined in Table 8.
2	t_{SPSCK}	SPSCK period	2 x t_{BUS}	2048 x t_{BUS}	ns	t_{BUS} = 1/ f_{BUS}
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{BUS} - 30	1024 x t_{BUS}	ns	—

Table continues on the next page...

6.8.5 I2S/SAI Switching Specifications

This section provides the AC timing for the I2S/SAI module in master mode (clocks are driven) and slave mode (clocks are input). All timing is given for noninverted serial clock polarity (TCR2[BCP] is 0, RCR2[BCP] is 0) and a noninverted frame sync (TCR4[FSP] is 0, RCR4[FSP] is 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the bit clock signal (BCLK) and/or the frame sync (FS) signal shown in the following figures.

All timing shown is also with respect to input signal transitions of 3 ns and a 50 pF maximum load.

Table 35. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time[1]	40		ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK cycle time (output)[1] I2S_RX_BCLK cycle time (output)[1]	80 160	— —	ns
S4	I2S_TX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	25	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns
S11	I2S_TX_FS input assertion to I2S_TXD output valid[2]	—	21	ns

1. This parameter is limited in VLPx modes.
2. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

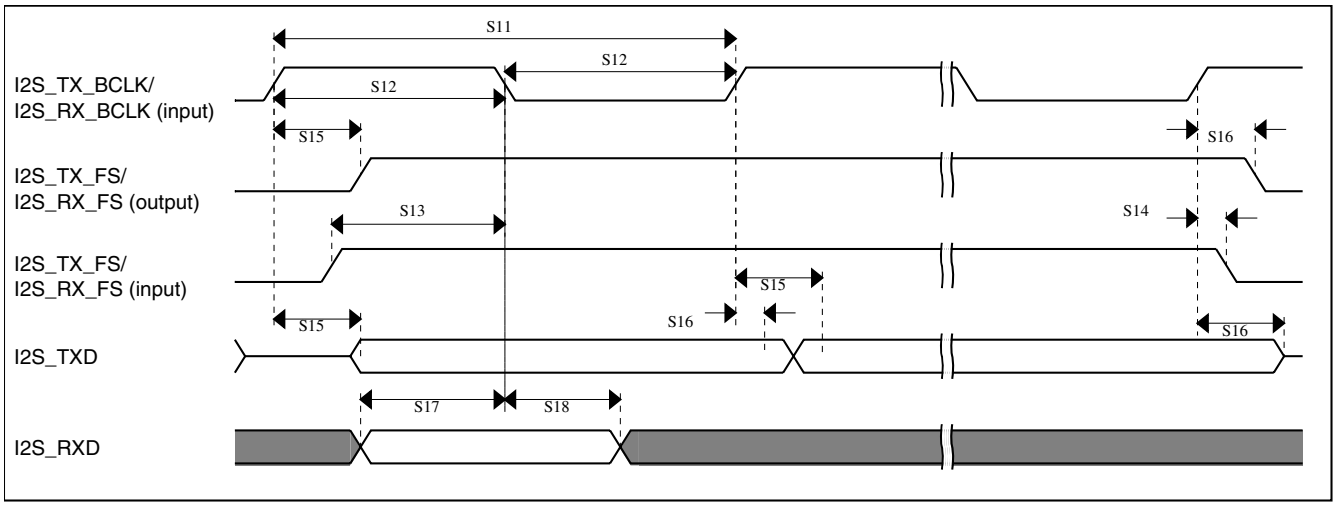

Figure 19. I2S/SAI timing — slave modes

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 37. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DDTSI}	Operating voltage	1.71	—	3.6	V	
C_{ELE}	Target electrode capacitance range	1	20	500	pF	1
f_{REFmax}	Reference oscillator frequency	—	5.5	14	MHz	2
f_{ELEmax}	Electrode oscillator frequency	—	0.5	4.0	MHz	3
C_{REF}	Internal reference capacitor	0.5	1	1.2	pF	
V_{DELTA}	Oscillator delta voltage	100	600	760	mV	4
I_{REF}	Reference oscillator current source base current • 1uA setting (REFCHRG=0) • 32uA setting (REFCHRG=31)	— —	1.133 36	1.5 50	µA	3 , 5
I_{ELE}	Electrode oscillator current source base current • 1uA setting (EXTCHRG=0) • 32uA setting (EXTCHRG=31)	— —	1.133 36	1.5 50	µA	3 , 6
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	%	7
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	%	8
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	%	9
MaxSens	Maximum sensitivity	0.003	12.5	—	fF/count	10
Res	Resolution	—	—	16	bits	
T_{Con20}	Response time @ 20 pF	8	15	25	µs	11

Table continues on the next page...

64-pin	48-pin	44-pin	32-pin	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
22	18	16	13	USB0_DP	USB0_DP								
23	19	17	14	VSS	VSS								
24	20	18	—	VDD	VDD								
25	21	19	15	ADC0_SE8/ TSI0_CH0	ADC0_SE8/ TSI0_CH0	PTA6		LPTMR_ALT1	FTM_FLT1	FBa_D7	FBa_AD17		
26	—	—	—	ADC0_SE9/ TSI0_CH1	ADC0_SE9/ TSI0_CH1	PTD2	FTM0_QD_PHA	RGPIO10	FTM0_CH0				
27	22	20	—	ADC0_SE10/TSI0_CH2	ADC0_SE10/TSI0_CH2	PTD3	FTM0_QD_PHB	RGPIO11	FTM0_CH1	FBa_D6	FBa_AD0		
28	—	—	—	ADC0_SE11/TSI0_CH3	ADC0_SE11/TSI0_CH3	PTD4		RGPIO12			FBa_D7		
29	—	—	—	ADC0_SE12/TSI0_CH4	ADC0_SE12/TSI0_CH4	PTD5		RGPIO13			FBa_D6		
30	23	21	16	ADC0_SE13/TSI0_CH5	ADC0_SE13/TSI0_CH5	PTA7	UART0_TX		FTM0_QD_PHA		FBa_D5		
31	24	22	—	ADC0_SE14/TSI0_CH6	ADC0_SE14/TSI0_CH6	PTD6	UART0_RX	RGPIO14			FBa_D4		
32	—	—	—	ADC0_SE15/TSI0_CH7	ADC0_SE15/TSI0_CH7	PTD7	UART0_CTS_b	I2C3_SCL	RGPIO15		FBa_D3		
33	—	—	—	TSI0_CH8	TSI0_CH8	PTE0	UART0_RTS_b	I2C3_SDA			FBa_D2		
34	—	—	—	TSI0_CH9	TSI0_CH9	PTE1	SPI0_SS		FTM_FLT0		FBa_D1		
35	25	23	17	IRQ/ EZP_MS_b	Disabled	PTB0		I2C0_SCL		IRQ/ EZP_MS_b			EZP_CS_b
36	26	24	18	TSI0_CH10	TSI0_CH10	PTB1	SPI0_SCLK	I2C0_SDA	FTM_FLT2	LPTMR_ALT2	FTM0_QD_PHB	FB_CLKOUT	
37	—	—	—	TSI0_CH11	TSI0_CH11	PTE2		I2C3_SCL			FBa_D0		
38	—	—	—	ADC0_SE16/ TSI0_CH12	ADC0_SE16/ TSI0_CH12	PTE3	SPI0_MOSI	I2C3_SDA			FBa_OE_b		
39	27	25	19	ADC0_SE17/ TSI0_CH13	ADC0_SE17/ TSI0_CH13	PTB2	SPI0_MISO				FBa_CS0_b		
40	28	26	20	ADC0_SE18/ TSI0_CH14	ADC0_SE18/ TSI0_CH14	PTB3	SPI0_MOSI			FBa_CS1_b	FBa_ALE		
41	29	—	—	ADC0_SE19/ TSI0_CH15	ADC0_SE19/ TSI0_CH15	PTE4	UART0_RTS_b	LPTMR_ALT3	SPI1_SS		FBa_AD1		
42	30	—	—	ADC0_SE20	ADC0_SE20	PTE5	UART0_CTS_b	I2C1_SCL	SPI1_SCLK		FBa_AD2		
43	—	—	—	ADC0_SE21	ADC0_SE21	PTE6	UART0_RX	I2C1_SDA	SPI1_MISO		FBa_AD3		
44	31	27	—	ADC0_SE22	ADC0_SE22	PTE7	UART0_TX	PDB0_EXTRG	SPI1_MOSI	FBa_RW_b	FBa_AD4		
45	32	28	21	BKGD/MS	Disabled	PTB4	BKGD/MS						
46	33	29	22	XTAL2	XTAL2	PTB5							